

Antonio Polimeni

List of Publications by Year in descending order

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248
papers

4,831
citations

81743

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55
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249
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249
docs citations

249
times ranked

3054
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 1 | Selective Effects of the Host Matrix in Hydrogenated InGaAsN Alloys: Toward an Integrated Matrix/Defect Engineering Paradigm. <i>Advanced Functional Materials</i> , 2022, 32, 2108862. | 7.8 | 0 |
| 2 | Energy Distribution in Tin Halide Perovskite. <i>Solar Rrl</i> , 2022, 6, 2100825. | 3.1 | 8 |
| 3 | Interplay of lattice, spin, and dipolar properties in CoTeMoO_6 : Emergence of Griffiths-like phase, metamagnetic transition, and magnetodielectric effect. <i>Physical Review B</i> , 2022, 105, . | 1.1 | 5 |
| 4 | Vibrational Properties in Highly Strained Hexagonal Boron Nitride Bubbles. <i>Nano Letters</i> , 2022, 22, 1525-1533. | 4.5 | 30 |
| 5 | Tailoring the optical properties of 2D transition metal dichalcogenides by strain. <i>Optical Materials</i> , 2022, 125, 112087. | 1.7 | 9 |
| 6 | Gap Opening in Double-Sided Highly Hydrogenated Free-Standing Graphene. <i>Nano Letters</i> , 2022, 22, 2971-2977. | 4.5 | 9 |
| 7 | Mechanical, Elastic, and Adhesive Properties of Two-Dimensional Materials: From Straining Techniques to State-of-the-Art Local Probe Measurements. <i>Advanced Materials Interfaces</i> , 2022, 9, . | 1.9 | 24 |
| 8 | Transport mechanisms in Co-doped ZnO (ZCO) and H-irradiated ZCO polycrystalline thin films. <i>Physical Chemistry Chemical Physics</i> , 2021, 23, 2368-2376. | 1.3 | 7 |
| 9 | Tailoring the optical properties of dilute nitride semiconductors at the nanometer scale. <i>Nanotechnology</i> , 2021, 32, 185301. | 1.3 | 0 |
| 10 | Brightly Luminescent and Moisture Tolerant Phenyl Viologen Lead Iodide Perovskites for Light Emission Applications. <i>Journal of Physical Chemistry Letters</i> , 2021, 12, 5456-5462. | 2.1 | 5 |
| 11 | Strain-tuning of the electronic, optical, and vibrational properties of two-dimensional crystals. <i>Applied Physics Reviews</i> , 2021, 8, . | 5.5 | 67 |
| 12 | Experimental Adhesion Energy in van der Waals Crystals and Heterostructures from Atomically Thin Bubbles. <i>Physical Review Letters</i> , 2021, 127, 046101. | 2.9 | 36 |
| 13 | Exceptional Elasticity of Microscale Constrained MoS_2 Domes. <i>ACS Applied Materials & Interfaces</i> , 2021, 13, 48228-48238. | 4.0 | 13 |
| 14 | Deuterium Adsorption on Free-Standing Graphene. <i>Nanomaterials</i> , 2021, 11, 130. | 1.9 | 14 |
| 15 | Towards free-standing graphane: atomic hydrogen and deuterium bonding to nano-porous graphene. <i>Nanotechnology</i> , 2021, 32, 035707. | 1.3 | 12 |
| 16 | Photoluminescence Spectroscopy Applied to Semiconducting Nanowires: A Valuable Probe for Assessing Lattice Defects, Crystal Structures, and Carriers' Temperature. , 2021, , 289-306. | | 0 |
| 17 | Nanoscale Measurements of Elastic Properties and Hydrostatic Pressure in H_2 -Bulged MoS_2 Membranes. <i>Advanced Materials Interfaces</i> , 2020, 7, 2001024. | 1.9 | 26 |
| 18 | Hole and Electron Effective Masses in Single InP Nanowires with a Wurtzite-Zincblende Homojunction. <i>ACS Nano</i> , 2020, 14, 11613-11622. | 7.3 | 8 |

| # | ARTICLE | IF | CITATIONS |
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| 19 | Opposite Hydrogen Behaviors in GaAsN and InAsN Alloys: Band Gap Opening Versus Donor Doping. Journal of Physical Chemistry C, 2020, 124, 19240-19251. | 1.5 | 5 |
| 20 | $N^{\sim}n^{\sim}H$ complexes in GaAs studied at the atomic scale by cross-sectional scanning tunneling microscopy. Physical Review B, 2020, 102, . | 1.1 | 4 |
| 21 | Imaging shape and strain in nanoscale engineered semiconductors for photonics by coherent x-ray diffraction. Communications Materials, 2020, 1, . | 2.9 | 2 |
| 22 | Broadband enhancement of light-matter interaction in photonic crystal cavities integrating site-controlled quantum dots. Physical Review B, 2020, 101, . | 1.1 | 14 |
| 23 | The Interaction of Hydrogen with the van der Waals Crystal $\text{I}^3\text{-InSe}$. Molecules, 2020, 25, 2526. | 1.7 | 11 |
| 24 | In-Situ Annealing and Hydrogen Irradiation of Defect-Enhanced Germanium Quantum Dot Light Sources on Silicon. Crystals, 2020, 10, 351. | 1.0 | 10 |
| 25 | Engineered Creation of Periodic Giant, Nonuniform Strains in MoS_2 Monolayers. Advanced Materials Interfaces, 2020, 7, 2000621. | 1.9 | 38 |
| 26 | Evidence of the direct-to-indirect band gap transition in strained two-dimensional WS_2 , MoS_2 , and WSe_2 . | 1.3 | 100 |
| 27 | Local magneto-optical response of H^+ irradiated $\text{Zn}_{1-x}\text{Co}_x\text{O}$ thin films. European Physical Journal: Special Topics, 2019, 228, 683-687. | 1.2 | 7 |
| 28 | Controlled Micro/Nanodome Formation in Proton-Irradiated Bulk Transition-Metal Dichalcogenides. Advanced Materials, 2019, 31, e1903795. | 11.1 | 60 |
| 29 | Giant magneto-optical response in H^+ irradiated $\text{Zn}_{1-x}\text{Co}_x\text{O}$ thin films. Journal of Materials Chemistry C, 2019, 7, 78-85. | 2.7 | 19 |
| 30 | Common nonlinear features and spin-orbit coupling effects in the Zeeman splitting of novel wurtzite materials. Physical Review B, 2019, 99, . | 1.1 | 13 |
| 31 | Unusual spin properties of InP wurtzite nanowires revealed by Zeeman splitting spectroscopy. Physical Review B, 2019, 99, . | 1.1 | 14 |
| 32 | Strain related relaxation of the GaAs-like Raman mode selection rules in hydrogenated $\text{GaAs}_{1-x}\text{N}_x$ layers. Journal of Applied Physics, 2019, 125, 175701. | 1.1 | 3 |
| 33 | Plasmon-assisted bandgap engineering in dilute nitrides. Nanophotonics, 2019, 8, 1465-1476. | 2.9 | 4 |
| 34 | Coupled Photonic Crystal Nanocavities as a Tool to Tailor and Control Photon Emission. Ceramics, 2019, 2, 34-55. | 1.0 | 2 |
| 35 | Spatially Selective Hydrogen Irradiation/Removal of Dilute Nitrides: A Versatile Nanofabrication Tool for Photonic Applications. , 2019, , . | | 0 |
| 36 | Spatially selective hydrogen irradiation of dilute nitride semiconductors: a brief review. Semiconductor Science and Technology, 2018, 33, 053001. | 1.0 | 5 |

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|----|---|------|-----------|
| 37 | Site-Controlled Single-Photon Emitters Fabricated by Near-Field Illumination. <i>Advanced Materials</i> , 2018, 30, e1705450. | 11.1 | 23 |
| 38 | Azetidinium lead iodide: synthesis, structural and physico-chemical characterization. <i>Journal of Materials Chemistry A</i> , 2018, 6, 10135-10148. | 5.2 | 16 |
| 39 | Gallium clustering and structural effects of hydrogenation in InGaN/GaN nanostructures. <i>Journal of Applied Physics</i> , 2018, 124, 165709. | 1.1 | 3 |
| 40 | Site-Controlled Quantum Emitters in Dilute Nitrides and their Integration in Photonic Crystal Cavities. <i>Photonics</i> , 2018, 5, 10. | 0.9 | 12 |
| 41 | A lithographic approach for quantum dot-photonic crystal nanocavity coupling in dilute nitrides. <i>Microelectronic Engineering</i> , 2017, 174, 16-19. | 1.1 | 10 |
| 42 | Addressing the Fundamental Electronic Properties of Wurtzite GaAs Nanowires by High-Field Magneto-Photoluminescence Spectroscopy. <i>Nano Letters</i> , 2017, 17, 6540-6547. | 4.5 | 10 |
| 43 | Electronic properties of wurtzite-phase InP nanowires determined by optical and magneto-optical spectroscopy. <i>Applied Physics Reviews</i> , 2017, 4, 041102. | 5.5 | 19 |
| 44 | In _x Ga _{1-x} As core-multi-shell nanowire quantum wells with tunable emission in the 1.3-1.5 μm wavelength range. <i>Nanoscale</i> , 2017, 9, 13554-13562. | 2.8 | 9 |
| 45 | Critical Temperature for the Conversion from Wurtzite to Zincblende of the Optical Emission of InAs Nanowires. <i>Journal of Physical Chemistry C</i> , 2017, 121, 16650-16656. | 1.5 | 2 |
| 46 | Effect of the order-disorder transition on the optical properties of Cu ₂ ZnSnS ₄ . <i>Applied Physics Letters</i> , 2016, 108, . | 1.5 | 53 |
| 47 | Long-Lived Hot Carriers in III-V Nanowires. <i>Nano Letters</i> , 2016, 16, 3085-3093. | 4.5 | 42 |
| 48 | Ferromagnetism and Conductivity in Hydrogen Irradiated Co-Doped ZnO Thin Films. <i>ACS Applied Materials & Interfaces</i> , 2016, 8, 12925-12931. | 4.0 | 25 |
| 49 | Value and Anisotropy of the Electron and Hole Mass in Pure Wurtzite InP Nanowires. <i>Nano Letters</i> , 2016, 16, 6213-6221. | 4.5 | 16 |
| 50 | Laser Level Scheme of Self-Interstitials in Epitaxial Ge Dots Encapsulated in Si. <i>Nano Letters</i> , 2016, 16, 6802-6807. | 4.5 | 27 |
| 51 | Bandgap Energy of Wurtzite InAs Nanowires. <i>Nano Letters</i> , 2016, 16, 5197-5203. | 4.5 | 47 |
| 52 | Genesis of Solitary Cations Induced by Atomic Hydrogen. <i>Advanced Functional Materials</i> , 2015, 25, 5353-5359. | 7.8 | 6 |
| 53 | Carrier masses and band-gap temperature sensitivity in Ga(AsBi) alloys. <i>Semiconductor Science and Technology</i> , 2015, 30, 094002. | 1.0 | 11 |
| 54 | Peculiarities of the hydrogenated In(AsN) alloy. <i>Semiconductor Science and Technology</i> , 2015, 30, 105030. | 1.0 | 4 |

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| 55 | Single photon emitters in dilute nitrides: Towards a determinist approach of quantum dot-photonic crystal nanocavity coupling. , 2015, , . | | 0 |
| 56 | Polarized Light Absorption in Wurtzite InP Nanowire Ensembles. Nano Letters, 2015, 15, 998-1005. | 4.5 | 44 |
| 57 | Temperature Dependence of Interband Transitions in Wurtzite InP Nanowires. ACS Nano, 2015, 9, 4277-4287. | 7.3 | 48 |
| 58 | H-tailored surface conductivity in narrow band gap In(AsN). Applied Physics Letters, 2015, 106, . | 1.5 | 4 |
| 59 | Synchrotron x-ray diffraction study of micro-patterns obtained by spatially selective hydrogenation of GaAsN. Applied Physics Letters, 2015, 106, 051905. | 1.5 | 3 |
| 60 | Nanoscale Tailoring of the Polarization Properties of Dilute-Nitride Semiconductors via H-Assisted Strain Engineering. Physical Review Applied, 2014, 2, . | 1.5 | 10 |
| 61 | H irradiation effects on the GaAs-like Raman modes in GaAs _{1-x} N _x /GaAs _{1-x} N _x :H planar heterostructures. Journal of Applied Physics, 2014, 116, . | 1.1 | 3 |
| 62 | Defect-induced magnetism in cobalt-doped ZnO epilayers. , 2014, , . | | 1 |
| 63 | Single Photons on Demand from Novel Site-Controlled GaAsN/GaAsN:H Quantum Dots. Nano Letters, 2014, 14, 1275-1280. | 4.5 | 32 |
| 64 | Hydrogen effects in dilute III-N-V alloys: From defect engineering to nanostructuring. Journal of Applied Physics, 2014, 115, 012011. | 1.1 | 9 |
| 65 | Magneto-Optical Properties of Wurtzite-Phase InP Nanowires. Nano Letters, 2014, 14, 4250-4256. | 4.5 | 23 |
| 66 | Connections between local and macroscopic properties in solids: The case of N in III-V-N alloys. Physical Review B, 2014, 89, . | 1.1 | 7 |
| 67 | Effect of thermal annealing on defects in post-growth hydrogenated GaNP. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 561-563. | 0.8 | 3 |
| 68 | Determination of Exciton Reduced Mass and Gyromagnetic Factor of Wurtzite (InGa)As Nanowires by Photoluminescence Spectroscopy under High Magnetic Fields. ACS Nano, 2013, 7, 10717-10725. | 7.3 | 15 |
| 69 | Effects of Bi incorporation on the electronic properties of GaAs: Carrier masses, hole mobility, and Bi-induced acceptor states. Physica Status Solidi (B): Basic Research, 2013, 250, 779-786. | 0.7 | 18 |
| 70 | Tuning of the optical properties of In-rich In _x Ga _{1-x} N (x=0.82~0.49) alloys by light-ion irradiation at low energy. , 2013, , . | | 0 |
| 71 | Effects of hydrogen irradiation on the optical and electronic properties of site-controlled InGaAsN V-groove quantum wires. , 2013, , . | | 1 |
| 72 | Excitonic recombination and absorption in In _x Ga _{1-x} As/GaAs heterostructure nanowires. Physical Review B, 2013, 87, . | 1.1 | 34 |

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| 73 | Nonresonant hydrogen dopants in In(AsN): A route to high electron concentrations and mobilities. Physical Review B, 2013, 87, . | 1.1 | 10 |
| 74 | Effects of hydrogen irradiation on the optical and electronic properties of site-controlled InGaAsN V-groove quantum wires. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 556-560. | 0.8 | 0 |
| 75 | A micrometer-size movable light emitting area in a resonant tunneling light emitting diode. Applied Physics Letters, 2013, 103, . | 1.5 | 3 |
| 76 | Resonant depletion of photogenerated carriers in InGaAs/GaAs nanowire mats. Applied Physics Letters, 2013, 102, . | 1.5 | 11 |
| 77 | Reduced temperature sensitivity of the polarization properties of hydrogenated InGaAsN V-groove quantum wires. Applied Physics Letters, 2012, 101, 151114. | 1.5 | 8 |
| 78 | Identification of four-hydrogen complexes in In-rich In _x Ga _{1-x} N | | |

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| 91 | Laser writing of the electronic activity of N- and H-atoms in GaAs. Applied Physics Letters, 2011, 99, 021105. | 1.5 | 10 |
| 92 | Optical study of hydrogen-irradiated GaAsN/GaAs heterostructures. Journal of Applied Physics, 2011, 109, 123511. | 1.1 | 11 |
| 93 | Hydrogen-mediated nanostructuring of dilute nitride semiconductors. Physica Status Solidi (B): Basic Research, 2011, 248, 1195-1202. | 0.7 | 0 |
| 94 | Fabrication of Site-Controlled Quantum Dots by Spatially Selective Incorporation of Hydrogen in Ga(AsN)/GaAs Heterostructures. Advanced Materials, 2011, 23, 2706-2710. | 11.1 | 41 |
| 95 | Room temperature spin filtering effect in GaNAs: Role of hydrogen. Applied Physics Letters, 2011, 99, 152109. | 1.5 | 7 |
| 96 | Deep levels in H-irradiated GaAs _{1-x} N _x (x≤ 0.01) grown by molecular beam epitaxy. Journal of Applied Physics, 2011, 110, . | 1.1 | 11 |
| 97 | Effect of postgrowth hydrogen treatment on defects in GaNP. Applied Physics Letters, 2011, 98, 141920. | 1.5 | 9 |
| 98 | Detailed structure of the H-N-H center in $\text{GaAs}_{1-x}\text{N}_x$ by vibrational spectroscopy under uniaxial stress. Physical Review B, 2010, 81, . | 1.1 | 19 |
| 99 | Quantum confinement effects in hydrogen-intercalated Ga _{1-x} As _x N _x -GaAs _{1-x} N _x :H planar heterostructures investigated by photoluminescence spectroscopy. Physical Review B, 2010, 81, . | 1.1 | 8 |
| 100 | Compositional dependence of the exciton reduced mass in GaAs _{1-x} B _x (x=0-10%). Physical Review B, 2010, 81, . | 1.1 | 48 |
| 101 | Hydrogen diffusion in GaAs _{1-x} N _x . Physical Review B, 2009, 80, . | 1.1 | 26 |
| 102 | Light polarization control in strain-engineered GaAsN/GaAsN:H heterostructures. Applied Physics Letters, 2009, 94, 261905. | 1.5 | 19 |
| 103 | Carrier mass measurements in degenerate indium nitride. Physical Review B, 2009, 79, . | 1.1 | 25 |
| 104 | Local structure of nitrogen-hydrogen complexes in dilute nitrides. Physical Review B, 2009, 79, . | 1.1 | 21 |
| 105 | Trends in the electronic structure of dilute nitride alloys. Semiconductor Science and Technology, 2009, 24, 033001. | 1.0 | 101 |
| 106 | Hydrogen-induced defect engineering in dilute nitride semiconductors. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 2644-2648. | 0.8 | 2 |
| 107 | Zero-phonon lines of nitrogen-cluster states in GaN _x As _{1-x} : H identified by time-resolved photoluminescence. Journal of Materials Science, 2008, 43, 4344-4347. | 1.7 | 2 |
| 108 | High-resolution X-ray diffraction in situ study of very small complexes: the case of hydrogenated dilute nitrides. Journal of Applied Crystallography, 2008, 41, 366-372. | 1.9 | 22 |

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| 109 | Photoluminescence under magnetic field and hydrostatic pressure for probing the electronic properties of GaAsN. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008, 205, 107-113. | 0.8 | 4 |
| 110 | Effective phonon bottleneck in the carrier thermalization of InAs/GaAs quantum dots. <i>Physical Review B</i> , 2008, 78, . | 1.1 | 26 |
| 111 | Effect of hydrogen incorporation temperature in in plane-engineered GaAsN ^x /GaAsN:H heterostructures. <i>Applied Physics Letters</i> , 2008, 92, 221901. | 1.5 | 14 |
| 112 | In-plane band gap modulation investigated by secondary electron imaging of GaAsN/GaAsN:H heterostructures. <i>Applied Physics Letters</i> , 2008, 93, 102116. | 1.5 | 9 |
| 113 | Secondary Electrons Characterization of Hydrogenated Dilute Nitrides. , 2008, , 541-542. | | 0 |
| 114 | Experimental evidence of different hydrogen donors in InN . <i>Physical Review B</i> , 2008, 77, . | 1.1 | 35 |
| 115 | Influence of bismuth incorporation on the valence and conduction band edges of GaAs _{1-x} Bix. <i>Applied Physics Letters</i> , 2008, 92, 262105. | 1.5 | 92 |
| 116 | Role of strain and properties of N clusters at the onset of the alloy limit in GaAs _{1-x} N _x . <i>Physical Review B</i> , 2008, 77, . | 1.1 | 18 |
| 117 | Vibrational properties of the H-N-H complex in dilute III-N-V alloys: Infrared spectroscopy and density functional theory. <i>Physical Review B</i> , 2008, 77, . | 1.1 | 23 |
| 118 | Controlled Band Gap Modulation of Hydrogenated Dilute Nitrides by SEM-Cathodoluminescence. <i>Springer Proceedings in Physics</i> , 2008, , 453-458. | 0.1 | 0 |
| 119 | Time-Resolved Photoluminescence of Nitrogen-Cluster States in Dilute Ga(NAs)/GaAs Heterostructures. , 2007, , . | | 0 |
| 120 | X-ray absorption and diffraction study of II-VI dilute oxide semiconductor alloy epilayers. <i>Journal of Physics Condensed Matter</i> , 2007, 19, 446201. | 0.7 | 2 |
| 121 | Photoreflectance and reflectance investigation of deuterium-irradiated GaAsN. <i>Applied Physics Letters</i> , 2007, 90, 091907. | 1.5 | 33 |
| 122 | Electron Mass in Dilute Nitrides and its Anomalous Dependence on Hydrostatic Pressure. <i>Physical Review Letters</i> , 2007, 98, 146402. | 2.9 | 42 |
| 123 | Formation and dissolution of D-N complexes in dilute nitrides. <i>Physical Review B</i> , 2007, 76, . | 1.1 | 42 |
| 124 | Hydrogen-induced Nitrogen Passivation in Dilute Nitrides: A Novel Approach to Defect Engineering. <i>Materials Research Society Symposia Proceedings</i> , 2007, 994, 1. | 0.1 | 0 |
| 125 | Investigation of Compositional Disorder in GaAsN:H. <i>AIP Conference Proceedings</i> , 2007, , . | 0.3 | 0 |
| 126 | Photoluminescence under magnetic field and hydrostatic pressure in GaAs _{1-x} N _x for probing the compositional dependence of carrier effective mass and gyromagnetic ratio. <i>AIP Conference Proceedings</i> , 2007, , . | 0.3 | 0 |

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| 127 | In-Plane Band Gap Engineering by Hydrogenation of Dilute Nitride Semiconductors. AIP Conference Proceedings, 2007, , . | 0.3 | 0 |
| 128 | Behavior of hydrogen in InN investigated in real time exploiting spectroscopic ellipsometry. Applied Physics Letters, 2007, 91, 081917. | 1.5 | 9 |
| 129 | Characteristics of InN grown on SiC under the In-rich regime by molecular beam heteroepitaxy. Applied Physics Letters, 2007, 90, 011910. | 1.5 | 16 |
| 130 | Vibrational spectroscopy of hydrogenated GaP $\hat{\sim}$ yNy. Physica B: Condensed Matter, 2007, 401-402, 347-350. | 1.3 | 0 |
| 131 | Thermal evolution of small N-D complexes in deuterated dilute nitrides revealed by in-situ high resolution X-ray diffraction. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 2766-2771. | 0.8 | 2 |
| 132 | Hydrostatic pressure experiments on dilute nitride alloys. Physica Status Solidi (B): Basic Research, 2007, 244, 24-31. | 0.7 | 3 |
| 133 | Influence of the Host Lattice on the O-H Interaction in II-VI Semiconductors. AIP Conference Proceedings, 2007, , . | 0.3 | 0 |
| 134 | Evidence of a New Hydrogen Complex in Dilute Nitride Alloys. AIP Conference Proceedings, 2007, , . | 0.3 | 0 |
| 135 | Correlation of band formation and local vibrational mode structure in Ga _{0.95} Al _{0.05} As $\hat{\sim}$ xNx with 0 $\hat{\sim}$ ox $\hat{\sim}$ % 0.03. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 619-622. | 0.8 | 3 |
| 136 | C _{2v} nitrogen-hydrogen complexes in GaAsN revealed by X-ray Absorption Near-Edge Spectroscopy and ab initio simulations. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1836-1840. | 0.8 | 0 |
| 137 | Unusual effects of hydrogen on electronic and lattice properties of GaNP alloys. Physica B: Condensed Matter, 2006, 376-377, 568-570. | 1.3 | 1 |
| 138 | Competition of N-passivation and Te-passivation in hydrogenation of Te-doped (Ga,In)(N,As). Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 218-221. | 1.3 | 1 |
| 139 | In-Plane Bandgap Engineering by Modulated Hydrogenation of Dilute Nitride Semiconductors. Advanced Materials, 2006, 18, 1993-1997. | 11.1 | 51 |
| 140 | Characterization of hydrogen passivated defects in strain-engineered semiconductor quantum dot structures. Journal of Applied Physics, 2006, 100, 084313. | 1.1 | 10 |
| 141 | Hydrogen-nitrogen complexes in dilute nitride alloys: Origin of the compressive lattice strain. Applied Physics Letters, 2006, 89, 061904. | 1.5 | 38 |
| 142 | Compositional disorder in GaAs $\hat{\sim}$ xNx:H investigated by photoluminescence. Physical Review B, 2006, 74, . | 1.1 | 16 |
| 143 | Influence of nitrogen-cluster states on the gyromagnetic factor of electrons in GaAs $\hat{\sim}$ xNx. Physical Review B, 2006, 74, . | 1.1 | 46 |
| 144 | Nitrogen-induced perturbation of the valence band states in GaP $\hat{\sim}$ xNx alloys. Physical Review B, 2006, 74, . | 1.1 | 12 |

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| 145 | Interaction between conduction band edge and nitrogen states probed by carrier effective-mass measurements in GaAs _{1-x} N _x . Physical Review B, 2006, 73, . | 1.1 | 106 |
| 146 | Passivation of an isoelectronic impurity by atomic hydrogen: The case of ZnTe:O. Applied Physics Letters, 2006, 88, 101910. | 1.5 | 22 |
| 147 | Defect passivation in strain engineered InAs/(InGa)As quantum dots. Materials Science and Engineering C, 2005, 25, 830-834. | 3.8 | 39 |
| 148 | High Energy Optical Transitions in Ga(PN): Contribution from Perturbed Valence Band. AIP Conference Proceedings, 2005, , . | 0.3 | 0 |
| 149 | Hydrogenation of Stacked Self-Assembled InAs/GaAs Quantum Dots. AIP Conference Proceedings, 2005, , . | 0.3 | 0 |
| 150 | Carrier localization in (InGa)(AsN) alloys (Invited Paper). , 2005, , . | | 0 |
| 151 | Free carrier and/or exciton trapping by nitrogen pairs in dilute GaP _{1-x} N _x . Physical Review B, 2005, 71, . | 1.1 | 22 |
| 152 | Effects of hydrogenation on the local structure of In _x Ga _{1-x} As _{1-y} N _y quantum wells and GaAs _{1-y} N _y epilayers. Physical Review B, 2005, 72, . | 1.1 | 12 |
| 153 | Nitrogen-hydrogen complex in GaAs _x N _{1-x} revealed by x-ray absorption spectroscopy. Physical Review B, 2005, 71, . | 1.1 | 56 |
| 154 | Comparison between experimental and theoretical determination of the local structure of the GaAs _{1-y} N _y dilute nitride alloy. Physical Review B, 2005, 71, . | 1.1 | 11 |
| 155 | Carrier relaxation dynamics in annealed and hydrogenated (GaIn)(NAs) _x GaAs quantum wells. Applied Physics Letters, 2005, 87, 252111. | 1.5 | 9 |
| 156 | Measurement of Carrier Localization Degree, Electron Effective Mass, and Exciton Size in In _x Ga _{1-x} As _{1-y} N _y Alloys. , 2005, , 223-251. | | 0 |
| 157 | Magnetophotoluminescence studies of In _x Ga _{1-x} As _{1-y} N _y : a measurement of the electron effective mass, exciton size, and degree of carrier localization. Journal of Physics Condensed Matter, 2004, 16, S3187-S3200. | 0.7 | 3 |
| 158 | Vibrational spectroscopy of hydrogenated GaAs _{1-y} N _y : a structure-sensitive test of an H ² (N) model. Physical Review B, 2004, 69, . | 1.1 | 41 |
| 159 | Tunable variation of the electron effective mass and exciton radius in hydrogenated GaAs _{1-x} N _x . Physical Review B, 2004, 69, . | 1.1 | 40 |
| 160 | Single carrier localization in In _x Ga _{1-x} As _{1-y} N _y investigated by magnetophotoluminescence. Applied Physics Letters, 2004, 84, 2295-2297. | 1.5 | 11 |
| 161 | Effect of lattice ionicity on hydrogen activity in II-VI materials containing isoelectronic oxygen impurities. IEE Proceedings: Optoelectronics, 2004, 151, 465-468. | 0.8 | 1 |
| 162 | Tuning of the electron effective mass and exciton wavefunction size in GaAs _{1-x} N _x . Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 747-751. | 1.3 | 1 |

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| 163 | Hydrogenation of strain engineered InAs/InxGa1-x As quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 581-584. | 0.8 | 2 |
| 164 | Role of hydrogen in improving optical quality of GaNAs alloys. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 20, 313-316. | 1.3 | 0 |
| 165 | Direct experimental evidence for unusual effects of hydrogen on the electronic and vibrational properties of GaNxP1-x alloys: A proof for a general property of dilute nitrides. Physical Review B, 2004, 70, . | 1.1 | 24 |
| 166 | Temperature dependence and bowing of the bandgap in ZnSe1-xOx. Applied Physics Letters, 2004, 84, 3304-3306. | 1.5 | 32 |
| 167 | Unusual properties of metastable (Ga,In)(N,As) containing semiconductor structures. IEE Proceedings: Optoelectronics, 2003, 150, 28. | 0.8 | 8 |
| 168 | Atomic ordering in (InGa)(AsN) quantum wells: An In K-edge X-ray absorption investigation. Nuclear Instruments & Methods in Physics Research B, 2003, 200, 34-39. | 0.6 | 8 |
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